

WOCSDICE 2018

WORKSHOP ON COMPOUND SEMICONDUCTOR DEVICES AND INTEGRATED CIRCUITS HELD IN EUROPE

BUCHAREST, ROMANIA, 14-16 MAY 2018

PROGRAM (version 07.05.2018)

Monday, 14 May 2018	Tuesday, 15 May 2018	Wednesday, 16 May 2018
WOCSDICE	WOCSDICE	WOCSDICE + EXMATEC
08:30 – 09:00 WOCSDICE Registration 09:00 – 09:15 Welcome to WOCSDICE 2018 (Mircea Dragoman, Conference Chairman) 09:15 – 09:45 Invited paper (Jaroslav Kovac, Slovakia) 09:45 – 10:45 GRAPHENE ELECTRONICS I <i>Chair: Hans Hartnagel, Germany</i> 10:45 – 11:00 Coffee break 11:00 – 11:30 Invited paper (Gregg Jessen, USA) 11:30 – 12:50 DEVICES I – HEMTs <i>Chair: Dimitris Pavlidis, USA</i> 13:00 – 14:00 Lunch 14:00 – 14:30 Invited paper (Rusty Harris, USA) 14:30 – 15:10 ADVANCED MATERIALS AND APPLICATIONS I, <i>Chair: Titus Sandu, Romania</i> 15:10 – 15:30 Coffee break 15:30 – 16:50 ADVANCED MATERIALS AND APPLICATIONS II, <i>Chair: Magdalena Ciurea, Romania</i> 19:00 – WOCSDICE Welcome Cocktail, GRAND HOTEL CONTINENTAL, Concerto Restaurant	09:00 – 09:30 Invited paper (Sorin Cristoloveanu, France) 09:30 – 10:30 GRAPHENE ELECTRONICS II <i>Chair: Sorin Cristoloveanu, France</i> 10:30 – 10:45 Coffee break 10:45 – 11:15 Invited paper (Alessandro Chini, Italy) 11:15 – 12:35 DEVICES II – GaN ELECTRONICS <i>Chair: Alessandro Chini, Italy</i> 12:45 – 14:00 Lunch 14:00 – 14:30 Invited paper (Naoteru Shigekawa, Japan) 14:30 – 15:50 HETEROSTRUCTURES <i>Chair: Naoteru Shigekawa, Japan</i> 16:00 – 19:00 Bucharest City Guided Tour 19:00 – WOCSDICE Gala Dinner, “Casa Doina” Restaurant	08:30 – 09:00 EXMATEC Registration 09:00 – 09:15 Welcome to EXMATEC 2018 (Mircea Dragoman, Conference Chairman) 09:15 – 10:15 WOCSDICE Invited papers (Alexandru Muller, Romania; Ikuo Soga, Japan) 10:15 – 11:15 THZ ELECTRONICS (WOCSDICE) <i>Chair: Hans Hartnagel, Germany</i> 11:15 – 11:30 Coffee break 11:30 – 12:30 ADVANCED MATERIALS AND APPLICATIONS III (WOCSDICE) <i>Chair: Alexandru Muller, Romania</i> 12:30 – 14:00 Lunch 14:00 – 15:00 EXMATEC Invited papers (Robert Czernecki, Poland; Giuseppe Greco, Italy) 15:00 – 16:40 GROWTH AND PROCESSING OF SEMICONDUCTORS AND OXIDES I (EXMATEC) <i>Chair: Dimitris Pavlidis, USA</i> 19:00 – EXMATEC Welcome Cocktail, GRAND HOTEL CONTINENTAL, Concerto Restaurant

	Monday, 14 May
	WOCSDICE 2018
08:30 – 09:00	WOCSDICE Registration
09:00 – 09:15	Welcome to WOCSDICE 2018 Mircea Dragoman, Conference Chairman
09:15 – 09:45	INVITED PAPER Characterization of electrothermal properties of GaN structures supported by 2/3D electrothermal modeling and simulation <u>Jaroslav Kovac</u> , Institute of Electronics and Photonics, Slovak University of Technology in Bratislava, Slovakia
09:45 – 10:05	GRAPHENE ELECTRONICS I <i>Chair: Hans Hartnagel, Germany</i>
10:05 – 10:25	Experimental investigations on Ni-catalyzed graphitization of PECVD deposited nanocrystalline graphene <u>Marius A. Avram</u> , F. Comănescu, S. Vulpe, O. Simionescu, F. Năstase, R. Gavrilă, A. Dinescu, M. Dănilă, V. Țucureanu, A. Matei, B. Țîncu, M. Veca, C. Pachi, O. Buiu, R. Popa National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania
10:25 – 10:45	Thin film graphene nanocomposite aerogels <u>Alexandru-Cosmin Obreja</u> ^{1*} , S. Iordanescu ¹ , M. Popescu ¹ , R. Gavrilă ¹ , V. Schiopu ¹ , F. Comanescu ¹ , M. Dragoman ¹ ¹ National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania
10:45 – 11:00	On Graphene Nanoribbon-based Nanoelectronic Circuits Viability <u>Sorin Cotofana</u> ^{1*} , P. Dimitrakis ² , M. Enachescu ³ , I. Karafyllidis ⁴ , A. Rubio ⁵ , G. Ch. Sirakoulis ⁴ ¹ Technical University of Delft, The Netherlands; ² Institute of Nanoscience and Nanotechnology, NCSR “Demokritos”, Greece; ³ “Politehnica” University of Bucharest, Romania; ⁴ Democritus University of Thrace, Greece; ⁵ Universitat Politècnica de Catalunya, BarcelonaTech, Spain
11:00 – 11:30	Coffee break
11:30 – 11:50	INVITED PAPER Electrical Characterization of Lateral Ga2O3 FETs for Power Switching and RF Power Applications <u>Gregg Jessen</u> ^{1*} , K. Chabak ¹ , A. Green, K. Leedy ¹ , A. Crespo ¹ , S. Tetlak ¹ , D. Walker Jr. ¹ , E. Heller ¹ ¹ Air Force Research Laboratory, WPAFB, OH 45433, USA
	DEVICES I – HEMTs <i>Chair: Dimitris Pavlidis, USA</i>
	Analysis of Thermal Properties of Power HEMT on SiC substrate <u>Aleš Chvála</u> ^{1*} , Robert Szobolovszky ¹ , Jaroslav Kováč jr. ¹ , Martin Florovič ¹ , Juraj Marek ¹ , Luboš Černaj ¹ , Patrik Příbytný ¹ , Daniel Donoval ¹ , Sylvain Laurent Delage ² , Jean-Claude Jacquet ² , Jaroslav Kováč ¹ ¹ Institute of Electronics and Photonics, Slovak University of Technology in Bratislava, Bratislava, Slovakia ² III-V Lab, Palaiseau, France

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11:50 – 12:10	Effect of Acceptor Density in Buffer Layer on Breakdown Characteristics of AlGaN/GaN HEMTs with High-k Passivation Layer S. Ueda, Y. Kawada, <u>K. Horio</u> [*] Faculty of Systems Engineering, Shibaura Institute of Technology, Saitama, Japan
12:10 – 12:30	Analysis of microwave detection with GaN HEMTs under RF probes Hector Sánchez-Martín ^{1*} , E. Pérez-Martín ¹ , P. Altuntas ² , V Hoel ² , S. Rennesson ³ , Y. Cordier ³ , J. A. Novoa ¹ , S. Pérez ¹ , T. González ¹ , J. Mateos ¹ , <u>I. Íñiguez-de-la-Torre</u> ¹ ¹ Universidad de Salamanca, Spain; ² Institut d'Électronique, de microélectronique et de nanotechnologie (IEMN), France; ³ Centre de Recherche sur l'Hétéro-Epitaxie et ses Applications, CNRS-CRHEA, France
12:30 – 12:50	High Transconductance Multiple Drain Access Channel AlGaN/GaN HEMTs Brendan Ubochi [*] , <u>Kaled Ahmeda</u> , M. Alqaysi, and K. Kalna Nanoelectronic Devices Computational (NanoDeCo) Group, College of Engineering, Swansea University, Swansea, Wales, United Kingdom.
13:00 – 14:00	Lunch
14:00 – 14:30	INVITED PAPER 3D (FinFET) integration of compound semiconductors with silicon <u>Rusty Harris</u> , Texas A&M University, USA
14:30 – 14:50	ADVANCED MATERIALS AND APPLICATIONS I <i>Chair: Titus Sandu, Romania</i> Low Temperature Direct Wafer Bonding of Thermally-Mismatched Materials <u>Viorel Dragoi</u> [*] , P. Kerepesi and N. Razek EV Group, St. Florian am Inn, AUSTRIA
14:50 – 15:10	Characterization of resistivity and breakdown field in Fe-doped semi-insulating GaN substrates <u>Kosuke Suzuki</u> ¹ , Atsuki Aoai ¹ , Joel T. Asubar ¹ , Hirokuni Tokuda ¹ , Kohei Nojima ² , Naoto Ishibashi ² , Narihito Okada ² , Kazuyuku Tadatomo ² , Masaaki Kuzuhara ¹ ¹ University of Fukui, Fukui, Japan; ² Yamaguchi University, Yamaguchi, Japan
15:10 – 15:30	Coffee break
15:30 – 15:50	ADVANCED MATERIALS AND APPLICATIONS II <i>Chair: Magdalena Ciurea, Romania</i> Ion Implantation for adjusting electrical conductivity of β-Ga₂O₃ by Nitrogen and Germanium Incorporation <u>Kornelius Tetzner</u> ¹ , E. Bahat-Treidel ¹ , A. Thies ¹ , G. Wagner ² , J. Würfl ¹ ¹ Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik, Berlin, Germany; ² Leibniz-Institut für Kristallzüchtung (IKZ), Berlin, Germany

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15:50 – 16:10	Models of thermal conductivity in ultrananocrystalline diamond films <u>Titus Sandu</u> [*] , Cristina Pachiu, Mihai Gologanu National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania
16:10 – 16:30	Impact of thermal treatment upon morphology and crystallinity of titanium nitride thin films deposited by RF sputtering <u>Silviu Vulpe</u> ^{1*} , F. Nastase ¹ , A. Avram ¹ , O. Simionescu ¹ , C. Romanitan ¹ , R. Gavrilă ¹ , B. Bită ^{1,2} , A. Dumitru ² ¹ National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania ² Faculty of Physics, University of Bucharest, PO Box MG-11, 077125, Magurele, Romania
16:30 – 16:50	Dielectrics choice and processing for low dispersion enhancement mode p-GaN gate HEMTs on 200mm Si substrates <u>Shuzhen You</u> ^{1*} , N. E. Posthuma ¹ , N. Ronchi ¹ , S. Stoffels ¹ , B. Bakeroort ² , D. Wellekens ¹ , H. Liang ¹ , M. Zhao ¹ , S. Decoutere ¹ ¹ IMEC, Leuven, Belgium; ² Centre for Microsystems Technology (CMST), IMEC and Ghent University, Gent, Belgium
19:00 – 21:00	WOCSDICE Welcome Cocktail , GRAND HOTEL CONTINENTAL, Concerto Restaurant

	Tuesday, 15 May
	WOCSDICE 2018
09:00 – 09:30	INVITED PAPER Novel concepts for nano-devices <u>Sorin Cristoloveanu</u> and Maryline Bawedin IMEP-LAHC, Grenoble INP Minatec, Grenoble, France GRAPHENE ELECTRONICS II <i>Chair: Sorin Cristoloveanu, France</i>
09:30 – 09:50	Graphene self-switching diodes for sub-millimetre wave harvesting applications Martino Aldrigo ^{1*} , M. Yasir ² , S. Iordanescu ¹ , D. Vasilache ¹ , A. Dinescu ¹ , M. Dragoman ¹ , M. Bozzi ² ¹ National Institute for Research and Development in Microtechnologies - IMT Bucharest, Romania; ² University of Pavia, Pavia, Italy
09:50 – 10:10	Two-Dimensional Layered Approaches for Devices Operating Using the Valley Degree of Freedom P. Sengupta ¹ , J. Shi ¹ and Dimitris Pavlidis ^{2*} ¹ University of Illinois, Chicago, Illinois, USA; ² Boston University, Boston, Massachusetts, USA
10:10 – 10:30	Detection of CO₂ Using MWCNT-Based Sensors <u>Alina Cismaru</u> ^{1*} , C. Obreja ¹ , M. Aldrigo ¹ , S. Iordanescu ¹ , B. Bit ¹ , M. Dragoman ¹ ¹ National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania
10:30 – 10:45	Coffee break
10:45 – 11:15	INVITED PAPER GaN RF and GaN Power – Device Parameter Drifts Analysis <u>Alessandro Chini</u> , <i>University of Modena and Reggio Emilia, Italy</i> DEVICES II – GaN ELECTRONICS <i>Chair: Alessandro Chini, Italy</i>
11:15 – 11:35	Ni based Schottky contacts in bulk GaN <u>Giuseppe Greco</u> ¹ , F. Giannazzo ¹ , M. Spera ^{1,2,3} , M. Cannas ³ , A. Alberti ¹ , F. Iucolano ⁴ , F. Roccaforte ¹ ¹ Istituto per la Microelettronica e Microsistemi (CNR-IMM), Catania, Italy; ² University of Catania, Catania, Italy; ³ University of Palermo, Palermo, Italy; ⁴ STMicroelectronics, Catania, Italy
11:35 – 11:55	Fabrication of quasi-vertical GaN JFET via Selective-Area Regrowth <u>Simon Kotzea</u> ^{1*} , A. Debal ¹ , M. Heuken ^{1,2} , H. Kalisch ¹ and A. Vescan ¹ ¹ CST, RWTH Aachen University, Aachen, Germany; ² AIXTRON SE, Herzogenrath, Germany

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11:55 – 12:15	Self-Aligned Processing of p-GaN-Gated E-mode HFET by Selective Etching with Cl₂/O₂/N₂ Gerrit Lükens ^{1*} , H. Hahn ¹ , M. Eickelkamp ² , M. Heuken ^{1,2} , H. Kalisch ¹ and A. Vescan ¹ 1 CST, RWTH Aachen University, Aachen, Germany; 2 AIXTRON SE, Germany
12:15 – 12:35	Reduction of threshold voltage for accumulation drifts in n-GaN MIS capacitors devices by post-metallization annealing Nicole Volkmer ¹ , Eldad Bahat Treidel ¹ , Franziska Naumann ² , Hassan Gargouri ² , Ina Ostermay ¹ , Oliver Hilt ¹ and Joachim Würfl ¹ 1 Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik, Berlin, Germany 2 SENTECH Instruments GmbH, Berlin, Germany
12:45 – 14:00	Lunch
14:00 – 14:30	INVITED PAPER Hybrid heterostructures and heterostructure devices fabricated by surface activated bonding technologies Naoteru Shigekawa, Graduate School of Engineering, Osaka City University, Japan HETEROSTRUCTURES Chair: Naoteru Shigekawa, Japan
14:30 – 14:50	Optical properties of as-grown GaAs/GaAsBi single quantum well structures grown by Molecular Beam Epitaxy Haifa Alghamdi ^{1*} , M. Henini ¹ , D. Fan ^{2, 3} , Y. I. Mazur ³ , M. E. Ware ^{2, 3} , S.-Q. Yu ^{2, 3} , G. J. Salamo ³ 1 University of Nottingham, Nottingham, UK; 2 Department of Electrical Engineering, University of Arkansas, Fayetteville, AR, USA. 3 Institute for Nanoscience and Engineering, University of Arkansas, Fayetteville, AR, USA
14:50 – 15:10	Coupling study in type II GaSb/GaAs quantum ring solar cells D. Montesdeoca ^{1*} , P.D. Hodgson ¹ , M. De La Mata ² , A.R.J. Marshall ¹ , S.I. Molina ² , P.J. Carrington ³ and A. Krier ¹ 1 Physics Department, Lancaster University, Lancaster, UK; 2 Facultad de Ciencias, IMEYMAT, Universidad de Cadiz, Campus Rio san Pedro, Cadiz, Spain; 3 Engineering Department, Lancaster University, Lancaster, UK
15:10 – 15:30	Broadband terahertz source based on wide-bandgap semiconductor quantum cascade structures for the detection of explosive materials Hans L. Hartnagel ^{1*} and Vadim P. Sirkeli ^{1,2} 1 Institut für Mikrowellentechnik und Photonik, Technische Universität Darmstadt, Darmstadt, Germany 2 Department of Information Technologies, Mathematics and Physics, Comrat State University, Comrat, Moldova
15:30 – 15:50	Sheet resistance under Ohmic contacts on AlGaIn/GaN heterostructures Monia Spera ^{1,2,3,*} , G. Greco ¹ , C. Miccoli ⁴ , R. Lo Nigro ¹ , C. Bongiorno ¹ , D. Corso ¹ , S. Di Franco ¹ , F. Iucolano ⁴ , F. Roccaforte ¹ 1 Istituto per la Microelettronica e Microsistemi (CNR-IMM), Catania, Italy; 2 University of Catania, Catania, Italy; 3 University of Palermo, Palermo, Italy; 4 STMicroelectronics, Catania, Italy
16:00 – 19:00	Bucharest City Guided Tour
19:00 – 22:00	WOCSDICE Gala Dinner, “Casa Doina” Restaurant

	Wednesday, 16 May
	WOCSDICE + EXMATEC 2018
08:30 – 09:00	EXMATEC Registration
09:00 – 09:15	Welcome to EXMATEC 2018 Mircea Dragoman, Conference Chairman
09:15 – 09:45	WOCSDICE INVITED PAPERS GaN SAW based sensors manufactured by micromachining and nanoprocessing of GaN/Si <u>Alexandru Muller</u> , National Institute for R&D in Microtechnologies - IMT Bucharest, Romania
09:45 – 10:15	MM-W and THz Circuitry Designs Based on InP and CMOS <u>Ikuo Soga</u> ^{1*} , Yoichi Kawano ¹ 1 Devices & Materials Laboratory, Fujitsu Laboratories Limited
10:15 – 10:35	THZ ELECTRONICS I (WOCSDICE) <i>Chair: Hans Hartnagel, Germany</i> Resonant tunneling hard-type oscillators having a Schottky diode trigger circuit for stable and large voltage swing operation <u>Koichi Maezawa</u> [*] , Motoyuki Yoshida, Masayuki Mori 1 Graduate School of Science and Engineering, University of Toyama
10:35 – 10:55	Near-ultraviolet avalanche photodetectors based on bulk ZnSe <u>Hans L. Hartnagel</u> ^{1*} , Vadim P. Sirkeli ^{1,2} , Oktay Yilmazoglu ³ , Ahid S. Hajo ¹ , Natalia D. Nedeoglo ⁴ , Dmitrii D. Nedeoglo ⁴ , Sascha Preu ¹ , and Franko Küppers ¹ 1 Institut für Mikrowellentechnik und Photonik, Technische Universität Darmstadt, Darmstadt, Germany; 2 Comrat State University, Comrat, Moldova; 3 Department of High Frequency Electronics, Technische Universität Darmstadt, Darmstadt, Germany; 4 Moldova State University, Chisinau, Moldova
10:55 – 11:15	A novel mechanical tuning element for SIW applications <u>Valentin Buiculescu</u> , Ioana Zdru, <i>National Institute for R&D in Microtechnologies - IMT Bucharest, Romania</i>
11:15 – 11:30	Coffee break
11:30 – 11:50	ADVANCED MATERIALS AND APPLICATIONS III (WOCSDICE) <i>Chair: Alexandru Muller, Romania</i> Effect of silicon surface cleaning on reliability of ALD HfO₂ films deposited from Tetrakis(dimethylamino)hafnium (TDMAH) <u>Cornel Cobianu</u> ^{1,2} , Florin Nastase ^{1,2} , Nicolae Dumbravescu ^{1,2} , Octavian Buiu ^{1,2} , Bogdan Serban ^{1,2} , Florin Comanescu ¹ , Raluca Gavrilă ¹ , Cosmin Romanitan ¹ , Octavian Ionescu ^{1,2} ; 1.National Institute for Research and Development in Microtechnologies - IMT Bucharest, ROMANIA

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11:50 – 12:10	2. Research Centre for Integrated Systems, Nanotechnologies and Carbon Based Nanomaterials (CENASIC) - IMT Bucharest, ROMANIA, Comparative study of structural and optical properties of Sm and La doped ZnO P. Pascariu ¹ , I. V. Tudose ² , C. Pachiu ³ , M. Danila ³ , R. Gavrilă ³ , E. Koudoumas ² , Mirela Sucheă ^{2,3*} 1 "Petru Poni" Institute of Macromolecular Chemistry, Iași, Romania; 2 Technological Educational Institute of Crete, Heraklion, Greece 3 National Institute for Research and Development in Microtechnologies - IMT Bucharest, Bucharest, Romania
12:10 – 12:30	Semiconducting metal oxides for ammonia and aliphatic amines gas sensing. A novel HSAB interaction paradigm B. C. Serban ^{1*} , O. Buiu ¹ , O. Ionescu ¹ , C. Cobianu ¹ , M. Brezeanu ² 1 National Institute for Research and Development in Microtechnologies - IMT Bucharest, Romania; 2 University Politehnica of Bucharest, Romania
12:30 – 14:00	Lunch
14:00 – 14:30	EXMATEC INVITED PAPERS Influence of hydrogen on InGaN quantum well MOVPE growth Robert Czernecki ^{1,2*} , E. Grzanka ^{1,2} , J. Smalc-Koziorowska ^{1,2} , S. Grzanka ^{1,2} , M. Leszczynski ^{1,2} ; ¹ Institute of High Pressure Physics of the Polish Academy of Sciences, Poland; ² TopGaN Ltd., Poland
14:30 – 15:00	Ohmic metallizations for GaN-based devices Giuseppe Greco ^{1*} , F. Iucolano ² , F. Roccaforte ² ; ¹ Consiglio Nazionale delle Ricerche – Istituto per la Microelettronica e Microsistemi (CNR-IMM), Italy; ² STMicronics, Italy
15:00 – 15:20	GROWTH AND PROCESSING OF SEMICONDUCTORS AND OXIDES I (EXMATEC) <i>Chair: Dimitris Pavlidis, USA</i> Preparation of ZnO:Al thin films by helicon wave excited magnetron sputtering method Shizutoshi Ando*, T. Namba, Tokyo University of Science, Japan
15:20 – 15:40	Oxide-free, electrically-conductive semiconductor interfaces fabricated by room temperature covalent direct bonding Viorel Dragoi*, C. Flötgen, N. Razek, EV Group E. Thallner GmbH, Austria
15:40 – 16:00	Atomic layer etching of AlGaIn Sebastien Aroulanda ^{1,2*} , O. Patard ¹ , N. Defrance ² , P. Altuntas ¹ , N. Michel ¹ , J. Pereira ¹ , P. Gamarra ¹ , C. Lacam ¹ , S. L. Delage ¹ , J.-C. de Jaeger ² , C. Gaquiere ² , ¹ III-V Lab, France ; ² Institut d'Electronique, de Microélectronique et de Nanotechnologie, France
16:00 – 16:20	MOCVD growth of thick In_xAl_{1-x}N (0.37 ≤ x ≤ 0.40) layer Prerna Chauhan ^{1*} , S. Hasenöhr ¹ , E. Dobročka ¹ , J. Kuzmík ¹ ; ¹ Institute of Electrical Engineering, Slovak Academy of Sciences, Slovak Republic
16:20 – 16:40	Nanoscale electrical characterization of graphene Schottky contacts onto AlGaIn/GaN heterostructures G. Greco ^{1*} , E. Schilirò ¹ , S. Di Franco ¹ , R. Lo Nigro ¹ , F. Roccaforte ¹ , F. Giannazzo ¹ , F. Iucolano ² , S. Ravesi ² , P. Prystawko ³ , P. Kruszewski ³ , M. Leszczyński ³ , R. Dagher ⁴ , E. Frayssinet ⁴ , A. Michon ⁴ , Y. Cordier ⁴ ; ¹ Consiglio Nazionale delle Ricerche – Istituto per la Microelettronica e Microsistemi (CNR-IMM), Italy; ² STMicronics, Italy; ³ TopGaN, Poland; ⁴ Université Côte d'Azur, CNRS, CRHEA, France
19:00 – 21:00	EXMATEC Welcome Cocktail , GRAND HOTEL CONTINENTAL, Concerto Restaurant